





An ISO/TS 16949, ISO 9001 and ISO 14001 Certified Company

PNP SILICON PLANAR EPITAXIAL TRANSISTORS



BC559, B, C BC560, B, C

TO-92 Plastic Package

Low Noise Transistors

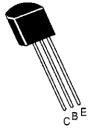
ABSOLUTE MAXIMUM RATINGS(Ta=25°C unless specified otherwise)

DESCRIPTION	SYMBOL	BC559	BC560	UNITS
Collector Emitter Voltage	V _{CEO}	30	45	V
Collector Base Voltage	$V_{\sf CBO}$	30	50	V
Emitter Base Voltage	$V_{\sf EBO}$	5	5	V
Collector Current Continuous	l _c	10	0	mA
Power Dissipation @ Tc=25°C	P _D	62	.5	mW
Derate Above 25°C		5	;	mW/ºC
Power Dissipation @ Tc=25°C	P_{D}	1.	5	W
Derate Above 25°C		1:	2	mW/°C
Operating And Storage Junction	$T_{j},\;T_{stg}$	-55 to	+150	°C
Temperature Range				
THERMAL RESISTANCE				
Junction to ambient	$R_{th(j-a)}$	20	00	°C/W
Junction to case	$R_{th(j-c)}$	83	.3	°C/W

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ELECTRICAL CHARACTERISTICS (Ta=25°C Unless Specified Otherwise)

DESCRIPTION			TEST CONDITION	MIN	TYP	MAX	UNITS
Collector Emitter Voltage							
	BC559	$V_{\sf CEO}$	l _C =10mA,l _B =0	30			V
	BC560			45			V
Collector Base Voltage							
•	BC559	V_{CBO}	I _C =10μΑ,I _E =0	30			٧
	BC560			50			V
Emitter Base Voltage		V_{EBO}	$I_E=10\mu A,\ I_C=0$	5			٧
Collector Cut off Current		Ісво	V _{CB} =30V, I _E = 0			15	nA
			$V_{CB} = 30V, I_{E} = 0$			5	μΑ
			Ta= +125°C				
Emitter Cut off Current		I _{EBO}	V _{CE} =40V, I _C =0			15	nA
		-250	VL				
DC Current Gain							
	В		V _{CE} =5V,I _C =10uA	100			
	С			100			
	В		V _{CE} =5V,I _C =2mA	180		460	
	С			380		800	
BC559,	, BC560			120		800	
Collector Emitter Saturation Ve	oltage						
	J	$V_{CE(sat)}$	l _C =10mA,l _B =0.5mA			0.25	V
		, .,,	I _C =100mA,I _B =see note 1			0.6	V
			I _C =100mA,I _B =5mA*		0.25		٧

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DESCRIPTION	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS
Base Emitter Saturation Voltage	$V_{\text{BE}(\text{sat})}$	I _C =100mA,I _B =5mA*		1.1		٧
Base Emitter On Voltage	$V_{BE(on)}$	I _C =10uA,V _{CE} =5V I _C =100uA,V _{CE} =5V		0.52 0.55		V V
		I _C =2mA,V _{CE} =5V	0.55		0.70	V

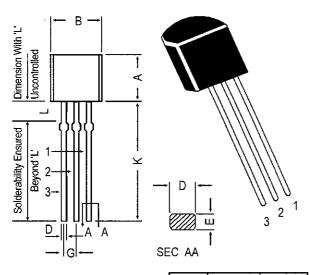
ELECTRICAL CHARACTERISTICS (Ta=25°C Unless Otherwise Specified)

DESCRIPTION	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS
DYNAMICS CHARACTERISTICS						
Transition Frequency	f_{T}	I _C =10mA, V _{CE} =5V				
		f=100MHz		250		MHz
Collector Base Capacitance	C_cbo	$V_{CB} = 10V$, $I_{E} = 0$, $f = 1MHz$		2.5		pF
Noise Figure	NF ₁	$V_{CE} = 5V_{.}I_{.C} = 200uA$ $R_{.S} = 2KW_{.}f = 30H_{.Z}$ To 15KHz			2.0	dB
	NF ₂	V _{CE} =5V ₁ I _C =200uA R _S =100KW,f=1.0KH _Z f=200Hz			10	dB
Small Signal Current Gain						
	B h _{fe}	$V_{CE} = 5V_{I} = 2mA$	240		500	
	С	f=1kH _Z	450		900	

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TO-92 Transistors on Tape and Ammo Pack



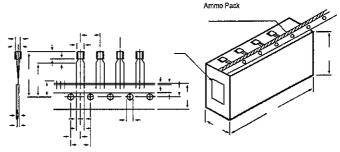
- F	1
3 2 1	TI O

PIN CONFIGURATION

- 1. EMITTER
- 2. BASE
- 3. COLLECTOR

DIM	MIN.	MAX.
Α	4.32	5.33
В	4.45	5.20
O	3.18	4.19
۵	0.41	0.55
ш	0.35	0.50
ᄔ	5 D	EG
G	1.14	1.40
I	1.14	1.53
K	12.70	
	1.982	2.082
	A B C D E F G H K	A 4.32 B 4.45 C 3.18 D 0.41 E 0.35 F 5 D G 1.14 H 1.14 K 12.70

All diminsions in mm.



All dimensions in mm unless specified otherwise

) TCM			SPECIFICATION			
ITEM	SYMBOL	MIN.	NOM.	MAX.	TOL.	REMARKS
BODY WIDTH BODY HEIGHT BODY THICKNESS	A1 A T	4.0 4.8 3.9		4.8 5.2 4.2	,	
PITCH OF COMPONENT FEED HOLE PITCH FEED HOLE CENTRE TO	P Po		12.7 12.7		±1 ±0.3	CUMULATIVE PITCH ERROR 1.0 mm/20 PITCH
COMPONENT CENTRE	P2		6.35		±0.4	TO BE MEASURED AT BOTTOM OF CLINCH
DISTANCE BETWEEN OUTER LEADS COMPONENT ALIGNMENT	F ∆h		5.08 0	1	+0.6 -0.2	AT TOP OF BODY
TAPE WIDTH HOLD-DOWN TAPE WIDTH HOLE POSITION	Wo Wo W1		8 6 9	, i	±0.5 ±0.2 +0.7 -0.5	AT TO: OF BODT
HOLD-DOWN TAPE POSITION LEAD WIRE CLINCH HEIGHT COMPONENT HEIGHT LENGTH OF SNIPPED LEADS	W2 H0 H1 L		0.5 16	23.25 11.0	±0.2 ±0.5	
FEED HOLE DIAMETER TOTAL TAPE THICKNESS LEAD - TO - LEAD DISTANCEF1,	Do t F2		4 2.54	1.2	±0.2 +0.4 -0.1	11 0.3 - 0.6
CLINCH HEIGHT PULL - OUT FORCE	H2 (P)	6N		3		

- NOTES

 1. MAXIMUM ALIGNMENT DEVIATION BETWEEN LEADS NOT TO BE GREATER THAN 0.2 mm.

 2. MAXIMUM NON-CUMULATIVE VARIATION BETWEEN TAPE FEED HOLES SHALL NOT EXCEED 1 mm IN 20 PITCHES.

 3. HOLDDOWN TAPE NOT TO EXCEED BEYOND THE EDGE(S) OF CARRIER TAPE AND THERE SHALL BE NO EXPOSURE OF ADHESIVE.

 4. NO MORE THAN 3 CONSECUTIVE MISSING COMPONENTS ARE PERMITTED.

 5. A TAPE TRAILER, HAVING AT LEAST THREE FEED HOLES ARE REQUIRED AFTER THE LAST COMPONENT.

 6. SPLICES SHALL NOT INTERFERE WITH THE SPROCKET FEED HOLES.

Notes

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Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Discrete Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished in the Data Sheet and on the CDIL Web Site/CD is believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Discrete Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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